

Aliases (04053-008Z, DLA Drawing 04053-008Z)

T496 HRA, Tantalum, MnO2 Tantalum, HRA, 4.7 uF, 20%, 6.3 VDC, SMD, MnO2, Molded, Military, Fused, High Reliability, A (Non-ER), 3.5 Ohms, 3528, Height Max = 2.1mm

CATHODE (-) END VIEW SIDE VIEW ANODE (+) END VIEW BOTTOM VIEW

Click	here	for	the	3D	model

Dimensions	
Footprint	3528
L	3.5mm +/-0.2mm
W	2.8mm +/-0.2mm
Н	1.9mm +/-0.2mm
Т	0.13mm REF
S	0.8mm +/-0.3mm
F	2.2mm +/-0.1mm
A	1.9mm MIN
В	0.4mm +/-0.15mm
E	2.2mm REF
G	1.8mm REF
Р	0.4mm REF
R	1.5mm REF
Χ	0.1mm +/-0.1mm

Packaging Specifications	
Packaging	T&R, 178mm
Packaging Quantity	2000

General Information	n
Series	T496 HRA
Dielectric	MnO2 Tantalum
Style	SMD Chip
Description	SMD, MnO2, Molded, Military, Fused, High Reliability
Features	Internal Fuse, High Reliability
RoHS	No
Prop 65	▲ WARNING: Cancer and reproductive harm - http://www.p65warnings.ca.gov.
SCIP Number	1dd2e1b8-26dd-4d52-927c-6f9d519011aa
Termination	Solder Coated
AEC-Q200	No
Component Weight	107.45 mg

Specifications	
Capacitance	4.7 uF
Capacitance Tolerance	20%
Voltage DC	6.3 VDC (85C), 4.22 VDC (125C)
Temperature Range	-55/+125°C
Rated Temperature	85°C
Dissipation Factor	6% 120Hz 25C
Failure Rate	A (Non-ER)
Resistance	3500 mOhms (100kHz 25C)
Leakage Current	0.3 uA (5min 25°C)
Testing and Reliability	Tested To Meet The Established Reliability

Statements of suitability for certain applications are based on our knowledge of typical operating conditions for such applications, but are not intended to constitute - and we specifically disclaim - any warranty concerning suitability for a specific customer application or use. This Information is intended for use only by customers who have the requisite experience and capability to determine the correct products for their application. Any technical advice inferred from this Information or otherwise provided by us with reference to the use of our products is given gratis, and we assume no obligation or liability for the advice given or results obtained.

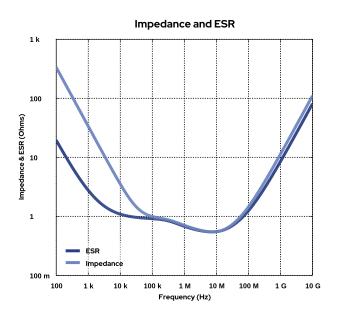


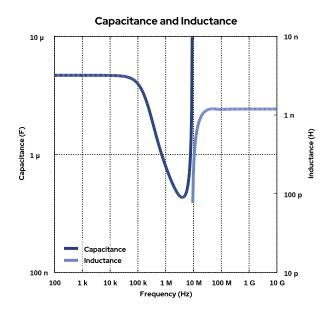
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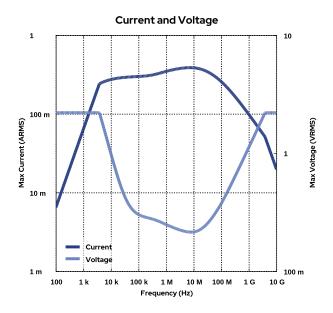
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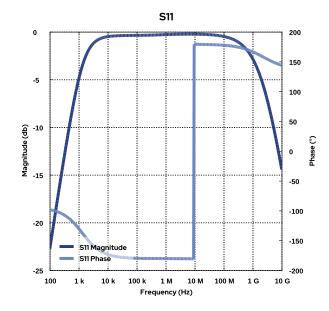
Simulations

For the complete simulation environment please visit K-SIM.





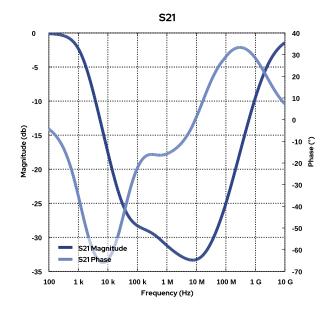






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These are simulations.

This is not a specification!

The responses shown represent the typical response for each part type. Specific responses may vary, depending on manufacturing variation affects of all parameters involved, including the specified tolerances applied to capacitance and unspecified variations of ESR, ESL, and leakage resistance.

The responses shown do not represent a specified or implied maximum capability of the device for all applications.

- The ESR used for ripple "Ripple Current/Voltage vs. Frequency" plots is the ESR at ambient temperature.
- The ESR in the "Temperature Rise vs. Ripple Current" plots is adjusted to each incremental temperature rise before the power and ripple current is calculated.
- The effects shown herein are based on measured data from a multiple part sample of the parts in question.
- Ripple capability of this device will be factored by thermal resistance (Rth) created by circuit traces (addi affects of all parameters involved, including the specified tolerances applied to capacitance and unspecified variations of ESR, ESL, and leakage resistance.

 The peak voltages generated in the "Temperature Rise vs. Combined Ripple Currents" plot are calculated for each frequency and are not combined with voltages generated at any other
- Please consult with the catalog or field applications engineer for maximum capability of the device in specific applications.

All product information and data (collectively, the "Information") are subject to change without notice.

KEMET K-SIM is designed to simulate behavior of components with respect to frequency, ambient temperature, and DC bias levels. The responses shown represent the typical response for each part type. Specific responses may vary, depending on manufacturing variation effects of all parameters involved, including the specified tolerances applied to capacitance and unspecified variations of ESR, ESL, and leakage resistance.

All Information given herein is believed to be accurate and reliable, but is presented without guarantee, warranty, or responsibility of any kind, expressed or implied. Statements of suitability for certain applications are based on our knowledge of typical operating conditions for such applications, but are not intended to constitute – and we specifically disclaim – any warranty concerning suitability for a specific customer application or use. This Information is intended for use only by customers who have the requisite experience and capability to determine the correct products for their application. Any technical advice inferred from this Information or otherwise provided by us with reference to the use of our products is given gratis, and we assume no obligation or liability for the advice given or results obtained.

If you have any questions please contact K-SIM.

单击下面可查看定价,库存,交付和生命周期等信息

>>KEMET(基美)